

VRRM	IF (TC≤135℃)	QC
650V	11A	23nC

Applications:

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

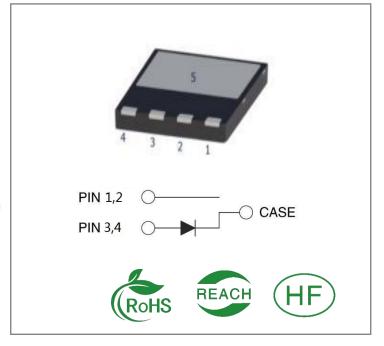
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSS10065R	DFN8*8	RSS10065R	Tape&reel	3000 PCS





Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VRRM	Repetitive Peak Reverse Voltage	650	V	TC = 25℃	
VRSM	Surge Peak Reverse Voltage	650	V	TC = 25°C	
VR	DC Blocking Voltage	650	V	TC = 25°C	
		28		TC ≤ 25°C	
IF	Forward Current	11	Α	TC ≤ 135°C	
		10		TC ≤ 140°C	
IFSM	Non-Repetitive Forward Surge Current	50 40	А	TC = 25° C, tp = 10ms, Half Sine Wave TC = 110° C, tp = 10ms, Half Sine Wave	
IFRM	Repetitive Peak Forward Surge Current	40	А	TC = 25° C, tp =10ms,Half Sine Wave	
Ptot	Power Dissipation	83	W	TC = 25°C	
TC	Maximum Case Temperature	140	$^{\circ}$		
TJ,TST	Operating Junction and Storage	-55	$^{\circ}$		
G	Temperature	to175			

Electrical Characteristics (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
VF	Forward Voltage	1.5	1.8	V	IF = 10A, TJ = 25℃	
VF	Forward Voltage	1.8		V	IF = 10A, TJ = 175℃	
ID	Reverse Current	10	80		VR = 650V, TJ = 25°C	
IR	Reverse Current	190		μΑ	VR = 650V, TJ = 175°C	
		387			VR = 1V, TJ = 25°C, f = 1MHz	
С	Total Capacitance	48	/	рF	VR = 200V, TJ = 25°C, f = 1MHz	
		33			VR = 400V, TJ = 25°C, f = 1MHz	
00	Total Capacitive	22	,	»C	\/D =400\/	
QC	Charge	23	/	nC	VR =400V,	

Thermal Characteristics (TJ= 25°C unless otherwise specified)

Symbol	ol Parameter		Unit	Note
RθJC	Thermal Resistance from Junction to Case	1.8	°C/W	



Typical Feature Curve

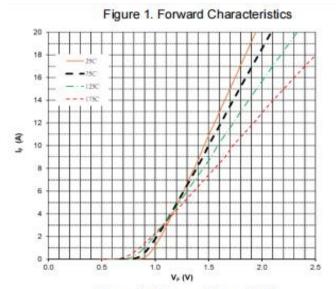


Figure 3. Reverse Characteristics

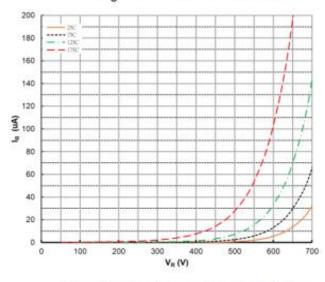


Figure 5. Capacitance vs Reverse Voltage

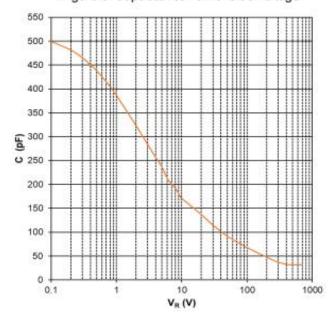


Figure 2. Forward Characteristics

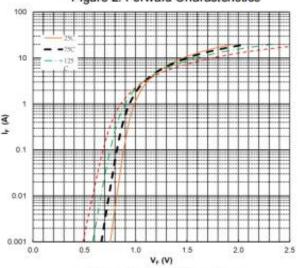


Figure 4. Power Derating

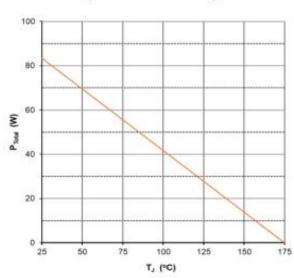
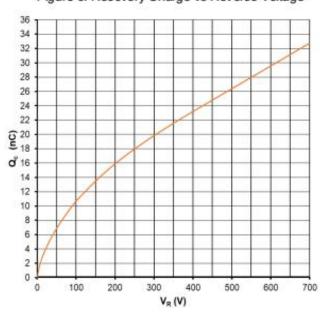
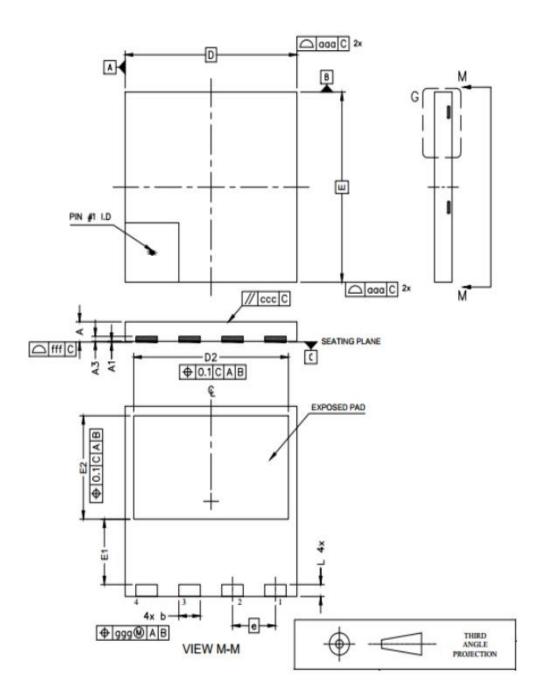


Figure 6. Recovery Charge vs Reverse Voltage





Package outline drawing(DFN8*8 Unit: mm)



lt	Millimeters				
Items	Min	Max			
Α	0.75	0.95			
A1	0.00	0.05			
A3	0.10	0.30			
b	0.9	1.10			
D	7.90	8.10			
E	7.90	8.10			
D2	7.10	7.30			
E1	2.65	2.85			
E2	4.25	4.45			
е	2.00 (BSC)				
L	0.40	0.60			
aaa	0.10				
999	0.05				
ccc	0.05				
fff	0.05				



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